P-Channel 30-V (D-S) MOSFET

Key Features:

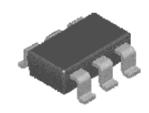
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

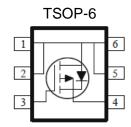
Typical Applications:

- Battery Powered Instruments
- Portable Computing
- Mobile Phones
- · GPS Units and Media Players

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
-30	54 @ V _{GS} = -10V	-5	
-30	75 @ V _{GS} = -4.5V	-4.2	







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage			-30	V	
Gate-Source Voltage	V_{GS}	±20	٧		
Continuous Drain Current a	T _A =25°C	· I _D	-5		
Continuous Drain Current	T _A =70°C	'D	-4	Α	
Pulsed Drain Current ^b	I _{DM}	-20			
Continuous Source Current (Diode Conduction) a	I _S	2.4	Α		
Power Dissipation ^a	T _A =25°C	P_{D}	2	W	
Fower Dissipation	T _A =70°C	'D	1.3	v V	
Operating Junction and Storage Temperature Range			-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	62.5	°C/W		
Maximum Junction-to-Ambient	Steady State	VθJA	110			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

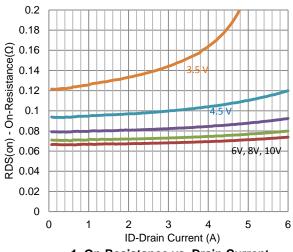
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \text{ uA}$				V	
Gate-Body Leakage	I _{GSS}	1 0// // .00//			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Gunerit	DSS	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10		
On-State Drain Current	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	10			Α	
Drain-Source On-Resistance	r	$V_{GS} = -10 \text{ V}, I_{D} = -4 \text{ A}$			54	mΩ	
Dialii-Source Off-Nesistance	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -3.6 \text{ A}$			75	11122	
Forward Transconductance	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -4 \text{ A}$		11		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 1.2 \text{ A}, V_{GS} = 0 \text{ V}$		0.78		V	
		Dynamic					
Total Gate Charge	Q_g			4.9			
Gate-Source Charge	Q_gs	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4 \text{ A}$		1.7		nC	
Gate-Drain Charge	Q_gd			2.3			
Turn-On Delay Time	t _{d(on)}			3.9			
Rise Time	t _r	$V_{DD} = -15 \text{ V}, R_L = 3.8 \Omega, I_D = -4 \text{ A},$		11.7		nc	
Turn-Off Delay Time	$t_{d(off)}$	V_{GEN} = -10 V, R_{GEN} = 6 Ω		19.1		ns	
Fall Time	t _f			10.1			
Input Capacitance	C _{iss}			356			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		38		pF	
Reverse Transfer Capacitance	C_{rss}]		17			

Notes

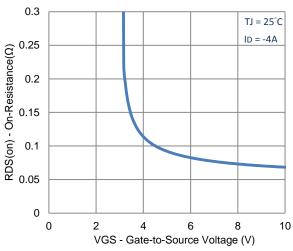
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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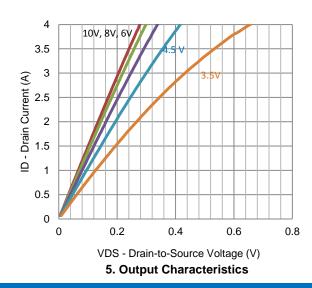
Typical Electrical Characteristics

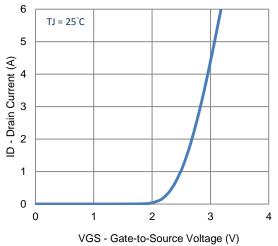


1. On-Resistance vs. Drain Current

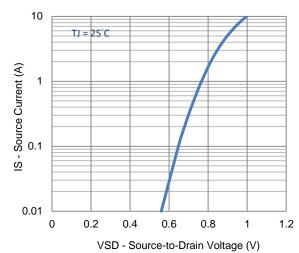


3. On-Resistance vs. Gate-to-Source Voltage

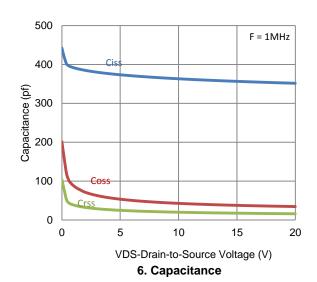




2. Transfer Characteristics

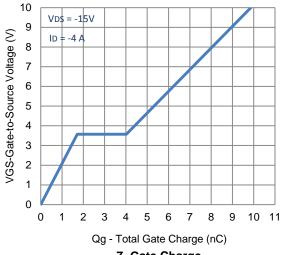


4. Drain-to-Source Forward Voltage



Typical Electrical Characteristics

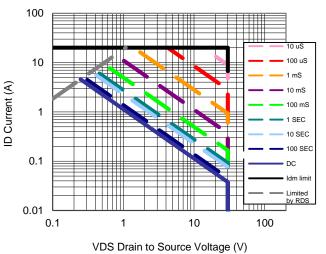
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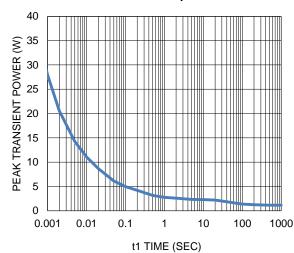


 $RDS(on) \text{ - }On\text{-}Resistance}(\Omega)$ (Normalized) 1.5 0.5 -50 -25 0 25 50 75 100 125 150

7. Gate Charge

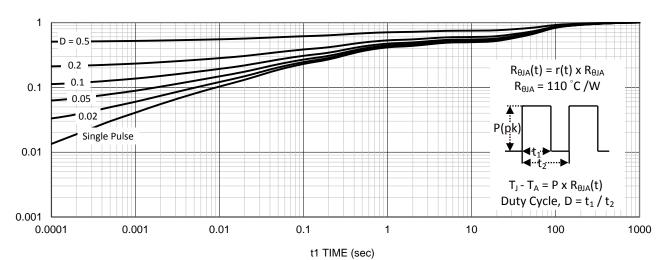






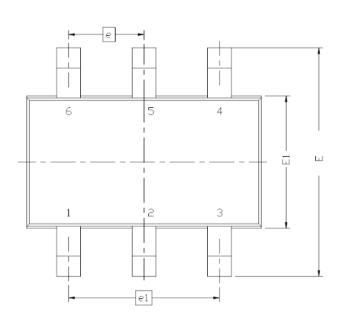
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation

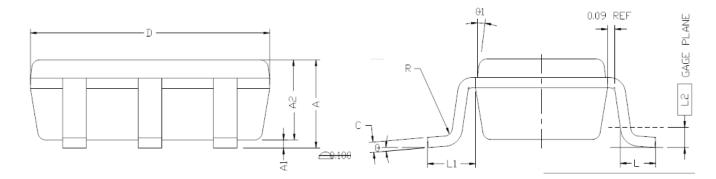


11. Normalized Thermal Transient Junction to Ambient

Package Information



DIM.	MILLIMETERS				
DIIVI.	MIN	NDM	MAX		
Α	0.935		1.10		
A1	0.01		0.10		
A2	0.70		1.00		
b	0.25	0.32	0.40		
C	0.10	0.15	0.20		
D	2.95	3.05	3.10		
Ε	2.70	2.85	2.98		
E1	1.55	1.65	1.70		
9	0.95 BSC				
L	0.30		0.60		
L1	0.60REF				
L2	0.25BSC				
R	0.10				
θ	0?	4?	8?		
θ1	7? N□M				



Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- 5. Dimension B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.